

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-30027A-B.

2. Structure :

- 2-1. Type : PIN diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy.
Back side (Cathode) : Gold.

3. Size :

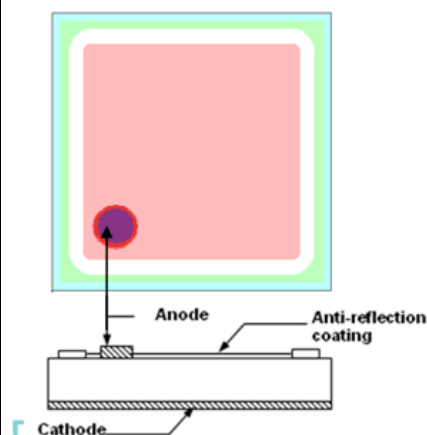
- 3-1. Chip size : 27.55 mils x 27.55 mils (0.700 mm x 0.700 mm).
- 3-2. Chip thickness : 8.66 ± 1.0 mils ($0.220 \text{ mm} \pm 0.025 \text{ mm}$).
- 3-3. Active area : 21.2 mils x 21.2 mils ($0.540 \text{ mm} \times 0.540 \text{ mm}$).
- 3-4. Bonding pad (Anode) : 3.94 ± 0.394 mils ($0.100 \pm 0.010 \text{ mm}$) diameter.
- 3-5. Pattern drawing : refer to the attached drawing

4. Absolute maximum rating (Ta = 25°C):

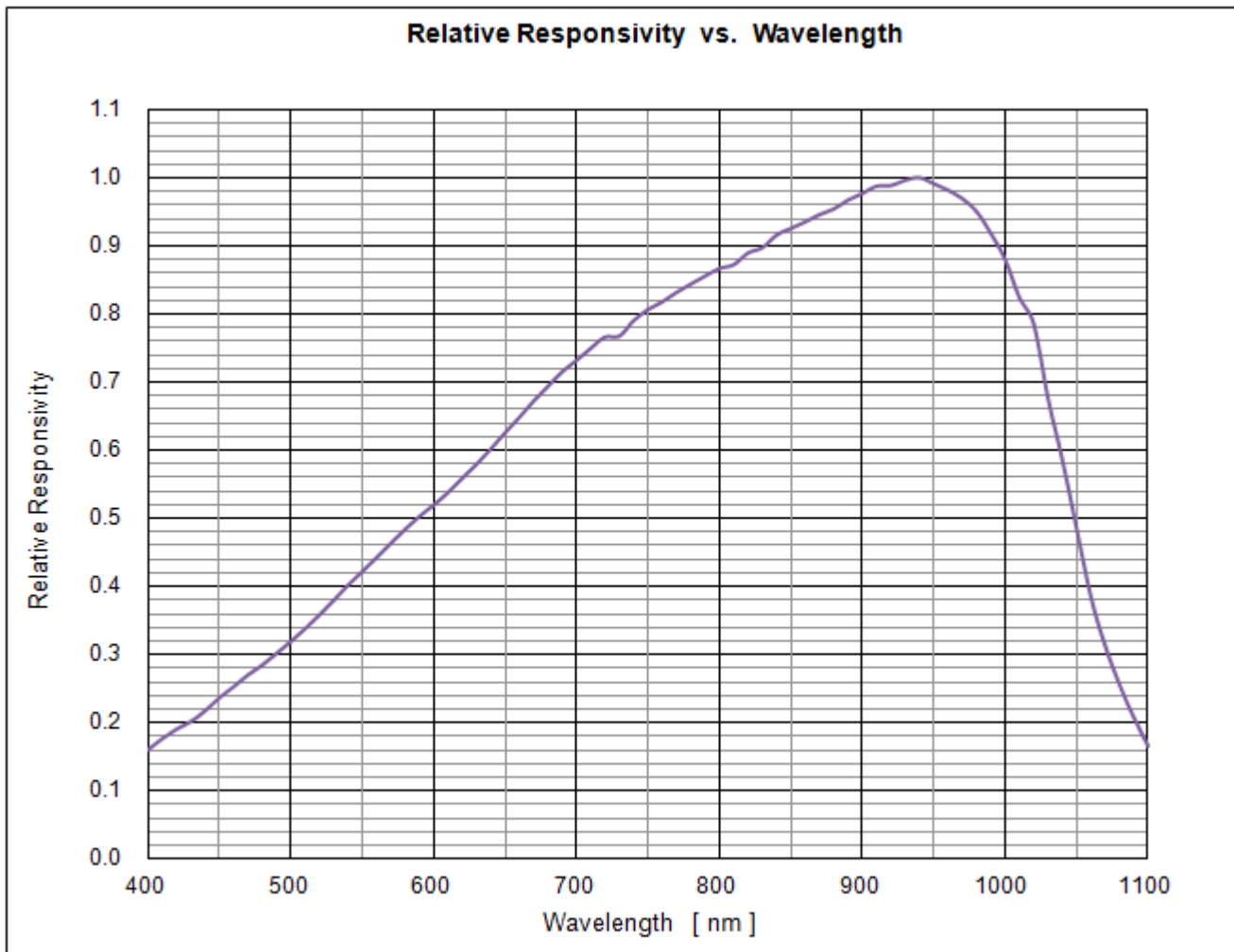
Parameter	Symbol	Rating	Unit
Reverse Voltage	VR	30	V
Operating temperature	Topr	-40~+85	°C
Storage temperature	Tstg	-40~+100	°C
Junction temperature	Tj	125	°C

5. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
* Reverse dark current	Id	VR=10V Ee=0mW/cm ²			10	nA
* Reverse breakdown voltage	V(BR)R	IR=100uA Ee=0mW/cm ²	60			V
Sensitivity Wavelength Range	λ	-	400		1100	nm
Peak sensitivity wavelength	λ_p	-		940		nm
Total Capacitance	CT	VR=0V Ee=0mW/cm ² f=1MHz		3.05		pF



6. Relative spectral response :



Bare chip measured, for reference only.